

# Performance Comparison

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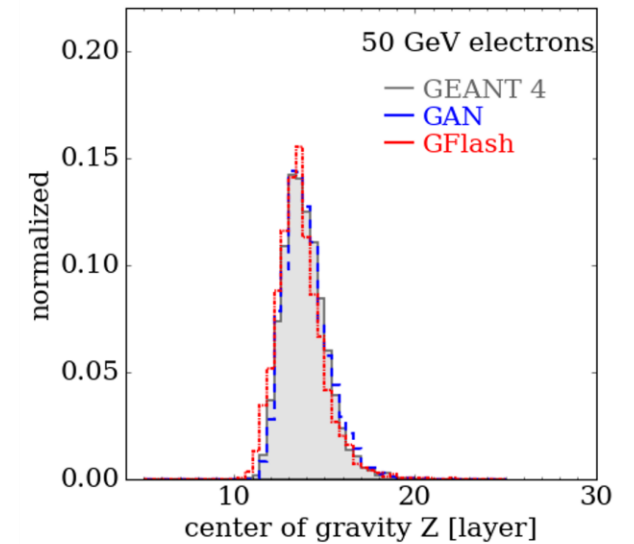
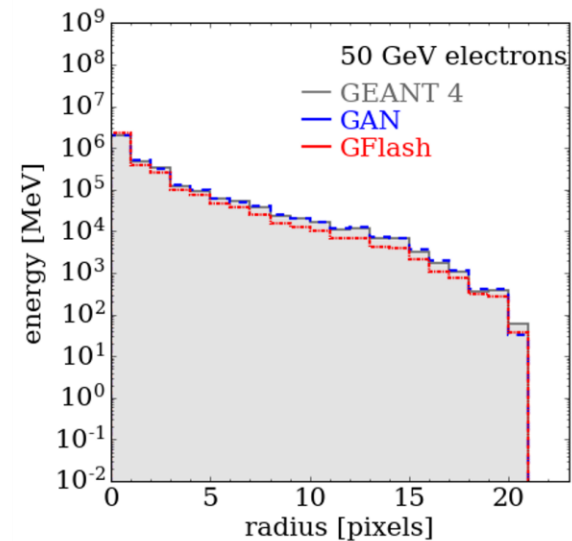
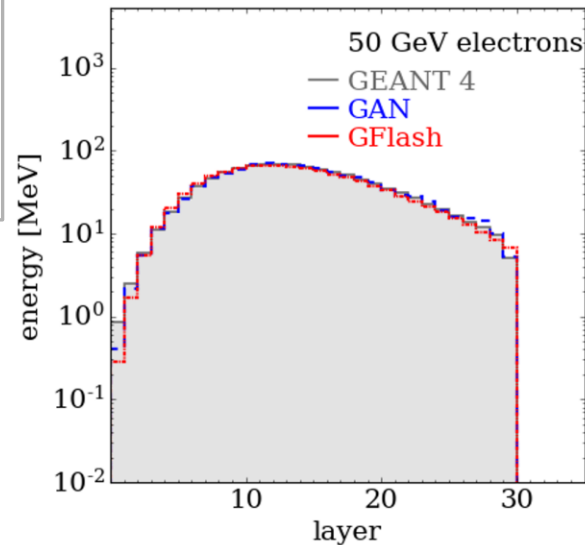
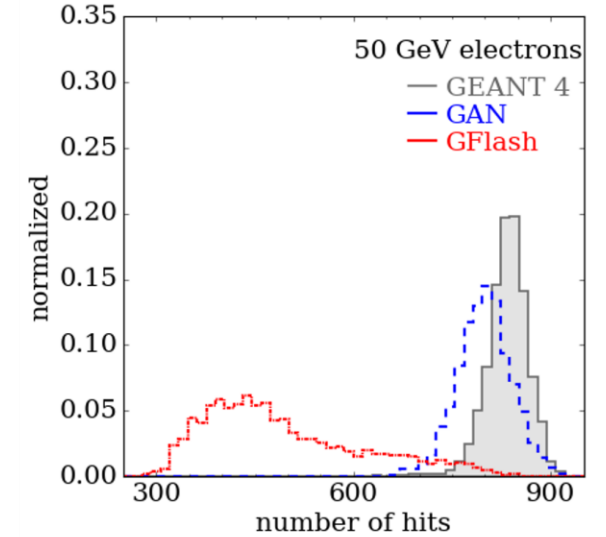
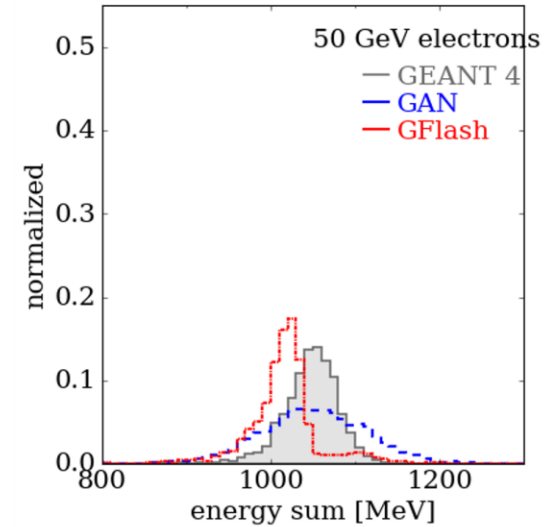
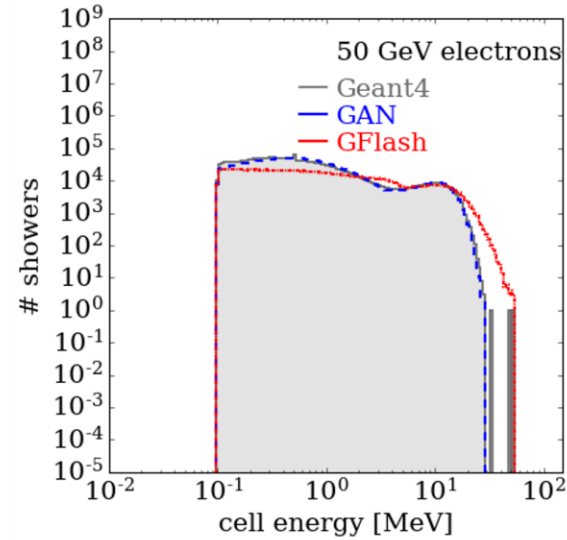
GEANT4, GFLASH, GAN

# Comparison of all Differential Distributions between Geant4, GFlash and the GAN Network

3200 showers  
50 GeV electrons  
Cut at 0.1 MeV

Shape: 30x30x30  
Absorber thickness = 5.5mm  
Sensitive thickness = 0.12mm

GFlash:  
Step size =  $0.001 * X_0$



# Area Difference

Geant4 & Gflash	Area Difference for each differential Distribution						
Energy [GeV]	Total E	Cell E	Occupancy	C. o. Gravity	Radial E	Logitudinal E	σ Area Difference
20	0.507	0.297	0.999	0.088	0.072	0.031	0.332
50	0.504	0.152	0.907	0.092	0.077	0.022	0.292
80	0.461	0.100	0.889	0.110	0.078	0.021	0.277
σ Area Difference for each Distribution	0.490	0.183	0.932	0.096	0.076	0.025	<b>0.300</b>

Table 1: Area Difference of 20, 50 and 80 GeV electron showers for six differential distributions between Geant4 and GFlash.

Factor: 2.24

Geant4 & GAN	Area Difference for each differential Distribution						
Energy [GeV]	Total E	Cell E	Occupancy	C. o. Gravity	Radial E	Logitudinal E	σ Area Difference
20	0.311	0.087	0.195	0.032	0.056	0.034	0.119
50	0.313	0.070	0.425	0.033	0.037	0.017	0.149
80	0.363	0.060	0.311	0.034	0.022	0.012	0.134
σ Area Difference for each Distribution	0.329	0.072	0.310	0.033	0.038	0.021	<b>0.134</b>

Table 2: Area Difference of 20, 50 and 80 GeV electron showers for six differential distributions between Geant4 and the GAN network.

# Computing Time

Model	Energy [GeV]	Computing Time on CPU [ms / shower]	Computing Time on GPU [ms / shower]
GAN	10 - 100	$80.774 \pm 1.171$	$5.579 \pm 0.0041$
GFlash*	10 - 100	149.969	-
Geant4	10 - 100	709,789	-

$$2 t_{\text{GAN, CPU}} = t_{\text{GF}}$$

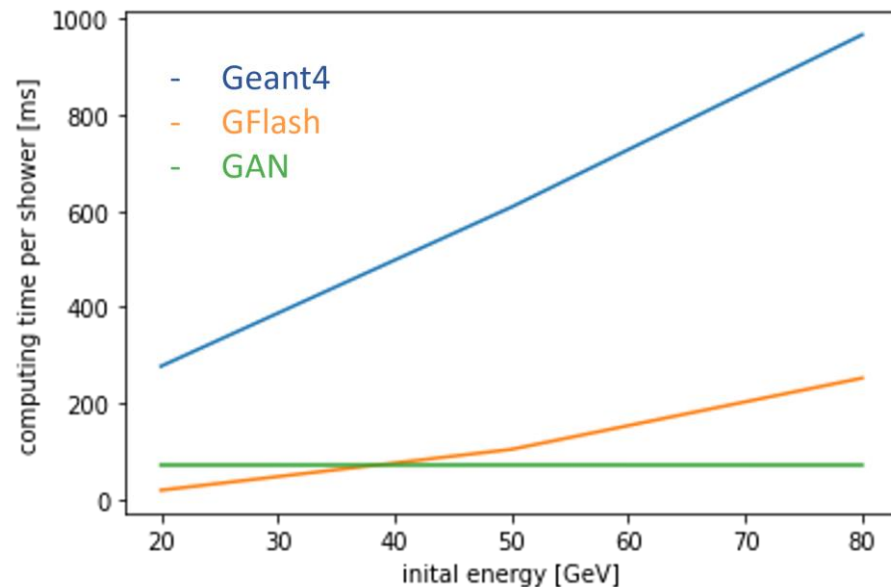
$$27 t_{\text{GAN, GPU}} = t_{\text{GF}}$$

$$9 t_{\text{GAN, CPU}} = t_{\text{G4}}$$

$$127 t_{\text{GAN, GPU}} = t_{\text{G4}}$$

\*step size is set to  $0.001 \cdot X_0$

## Computing t for various electron energies



## GFlash Computing t for various step sizes

